



**COLLEGE OF ENGINEERING
PUTRAJAYA CAMPUS
FINAL EXAMINATION
SEMESTER 2 2012 / 2013**

PROGRAMME : **Bachelor of Electrical & Electronics Engineering (Honours)
Bachelor of Electrical Power Engineering (Honours)**

SUBJECT CODE : **EEEB273**

SUBJECT : **ELECTRONIC ANALYSIS AND DESIGN II**

DATE : **January 2013**

TIME : **3 hours**

INSTRUCTIONS TO CANDIDATES:

1. This paper contains **Five (5)** questions in **Ten (10)** pages.
2. Answer **ALL** questions.
3. Write **all** answers in the answer booklet provided.
4. Write answer to different question on a **new page**.
5. For all calculations, assume that $V_T = 26 \text{ mV}$.
6. Use at least **4 significant numbers** in all calculations.

THIS QUESTION PAPER CONSISTS OF TEN (10) PRINTED PAGES INCLUDING THIS COVER PAGE.

Question 1 [15 marks]

(a) For a **BJT Cascode current source (using npn transistors)** with $R_1 = 9.3 \text{ k}\Omega$, the transistor parameters are $V_{BE(\text{on})} = 0.7 \text{ V}$, $\beta = 120$, and $V_A = 100 \text{ V}$. The bias voltages are $V^+ = 5 \text{ V}$ and $V^- = -5 \text{ V}$.

(i) **Draw the circuit for the BJT Cascode current source specified above.** Label the circuit clearly. [2 marks]

(ii) **Show that the relationship between I_O and I_{REF}** can be given by the following equation. [5 marks]

$$I_O \cong \frac{I_{REF}}{1 + 4/\beta}$$

Hints: You may start by using equation $I_{E4} = I_{E3} / (1+2/\beta)$ derived for a **BJT two-transistor current source**.

(b) A **MOSFET two-transistor (using NMOS) current source** is using a resistor to establish its I_{REF} . The output current (I_O) is **1 mA** and the circuit parameters are $V^+ = 15 \text{ V}$ and $V^- = -15 \text{ V}$. Assume all transistors are identical. The transistor parameters are $V_{DS(\text{sat})} = 0.8 \text{ V}$, $V_{TN} = 1.5 \text{ V}$, $k'_n = 50 \mu\text{A}/\text{V}^2$ and $\lambda = 0$.

(i) Let the second transistor, M_2 , be the output transistor. **Draw and label** the circuit and its components **clearly**. **Hints:** You need to determine the value of R_1 in order to draw and label the circuit **correctly**. [2 marks]

(ii) **Calculate the aspect ratios** for all transistors. [2 marks]

(iii) **Find the change on the output current** due to changes on the output voltage from **2 to 10 Volt**. [2 marks]

(iv) **Discuss how** the reference portion of the circuit can be designed with MOSFETs. [2 marks]

Question 2 [20 marks]

(a) Consider the differential amplifier in **Figure 2a** where **one-sided output** is taken at V_{D2} . It is given that $R_D = 18 \text{ k}\Omega$, $K_n = 125 \mu\text{A}/\text{V}^2$, $\lambda = 0$, $A_{cm} = 0.2$, and $CMRR$ of the differential amplifier is **55 dB**.

(i) Find I_Q . [6 marks]

(ii) Instead of increasing the value of R_D , **suggest how** the circuit can be modified to get a bigger $CMRR$. [3 marks]

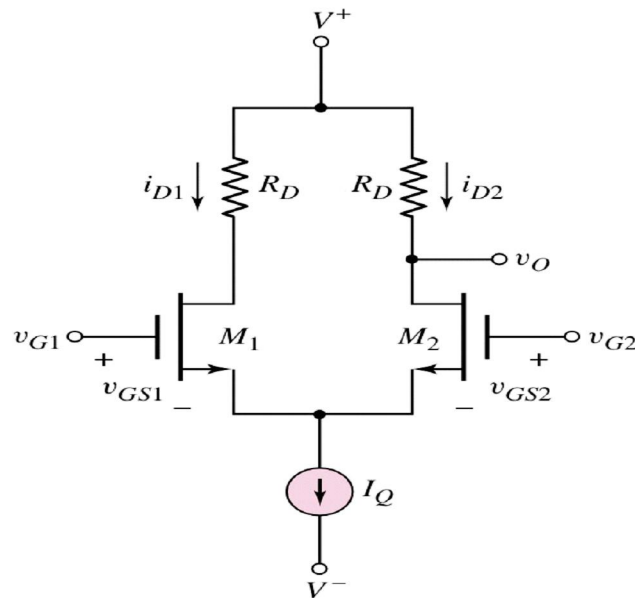


Figure 2a

(b) The differential amplifier shown in **Figure 2b** has a **three-transistor current mirror** connected as an **active load**. The circuit is connected to power supply voltages of $V^+ = +5$ V and $V^- = -5$ V.

(i) **Derive** the relationship between I_O and I_Q such that the amplifier **dc currents are balanced**. State your assumptions. [9 marks]

(ii) **Calculate** the value of I_O given that $I_Q = 0.2$ mA and $\beta = 120$. [2 marks]

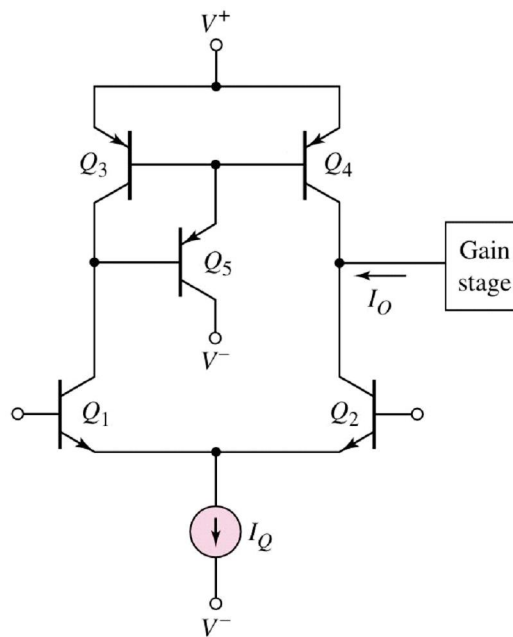


Figure 2b

Question 3 [25 marks]

- (a) A simple **bipolar op-amp** is designed as shown in **Figure 3a**. Note that biasing for amplifiers in the circuit is provided by two-transistor current mirrors. Study the figure carefully. **Neglect base currents.** Assume parameters for all transistors are: $V_{BE(on)} = 0.7 \text{ V}$, $\beta = 120$, and $V_A = \infty$.

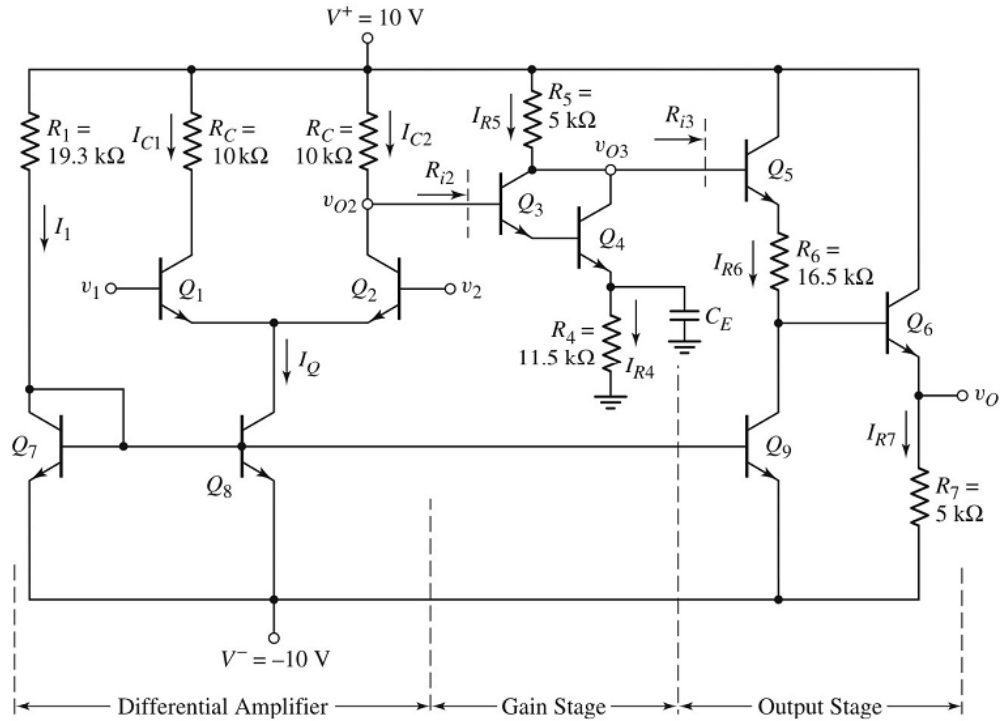


Figure 3a

- (i) Referring to **Figure 3a**, find $I_1, I_Q, I_{C2}, v_{O2},$ and v_{O3} . [5 marks]
- (ii) With small-signal analysis values for $A_{d1}, r_{\pi3}, R_{i2},$ and A_2 can be found using the following formula:

$$A_{d1} = \left(\frac{V_{o2}}{v_d} \right) = \frac{g_m}{2} (R_C \parallel R_{i2})$$

$$r_{\pi3} \cong \beta r_{\pi4}$$

$$R_{i2} = r_{\pi3} + (1 + \beta)r_{\pi4}$$

$$A_2 \cong \frac{I_{R4}}{2V_T} (R_5)$$

Calculate $A_{d1}, A_2,$ and the total overall small-signal voltage gain, A_d .

[10 marks]

(b) Consider the MC14573 op-amp in Figure 3b. Assume transistors parameters of $V_{TN} = 0.5$ V, $V_{TP} = -0.5$ V, $K_n = 125 \mu\text{A}/\text{V}^2$, $K_p = 100 \mu\text{A}/\text{V}^2$, $V_{SG5} = 1.5$ V, $\lambda_n = 0.01\text{V}^{-1}$, $\lambda_p = 0.02\text{V}^{-1}$ and the circuit parameters of $V^+ = 10$ V, $V^- = -10$ V.

(i) Find the dc bias currents I_Q . [3 marks]

(ii) Determine the overall voltage gain of the op-amp. [7 marks]

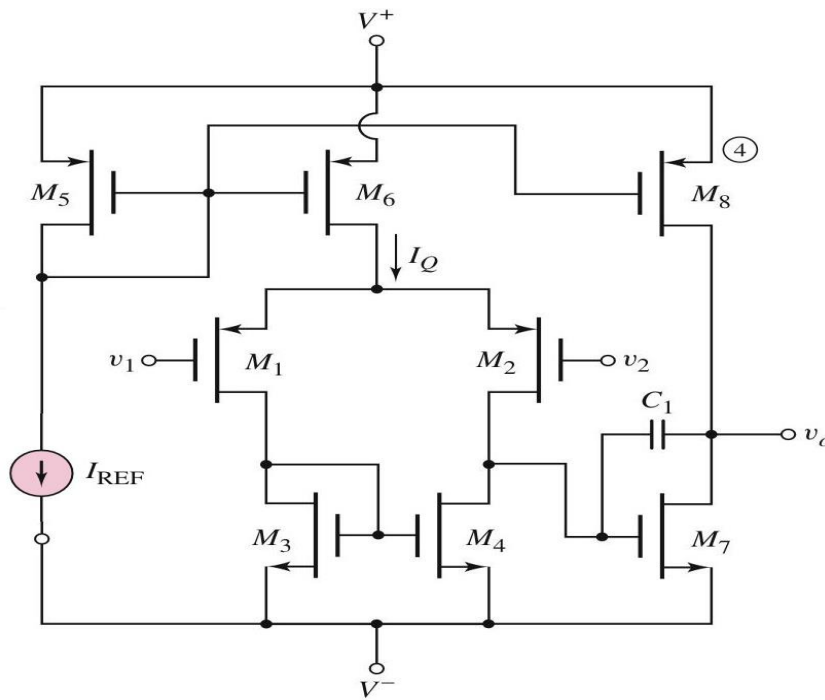


Figure 3b

Question 4 [15 marks]

Study the output stage circuit shown in **Figure 4** carefully. Let $R_L = 1 \text{ k}\Omega$, $V_{BB} = 1.40 \text{ V}$ and the reverse saturation current for the transistors, $I_S = 2 \times 10^{-15} \text{ A}$. Assume $\beta \gg 1$.

- (a) **Explain** the "cross-over distortion" phenomenon in **class-B output stage**. [3 marks]

- (b) What is the **advantage** of the output stage shown in **Figure 4** compared to the **class-A** and **class-B** output stages? [2 marks]

- (c) Referring to **Figure 4**, for the case of the output voltage $v_O = -3.5 \text{ V}$, **determine** i_L , i_{Cn} , and i_{Cp} . [6 marks]

- (d) Referring to **Figure 4**, for the case of the output voltage $v_O = -3.5 \text{ V}$, **calculate** the power dissipated in transistor Q_n and Q_p . [4 marks]

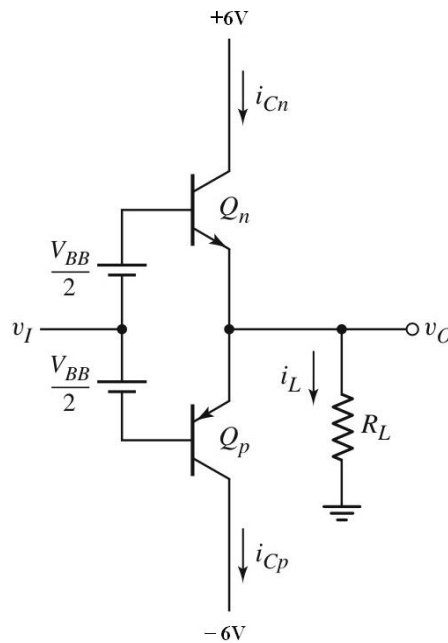


Figure 4

Question 5 [25 marks]

- (a) List two (2) ideal operational amplifier characteristics. [2 marks]
- (b) State three (3) applications of an ideal operational amplifier. [3 marks]
- (c) For an **amplifier circuit** using op-amps shown in **Figure 5a**, use appropriate ideal op-amp characteristics and **superposition theorem** to show that

$$v_O = v_{I1} + v_{I2}$$

when $R_1 = R_2 = R_F = 100 \text{ k}\Omega$. [7 marks]

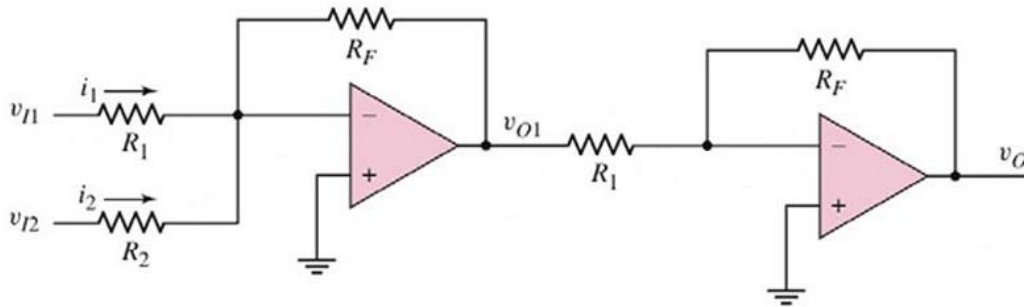


Figure 5a

- (d) Find the voltage gain, A_v , for the op-amp circuit in **Figure 5b**. Assume the op-amp is ideal. [5 marks]

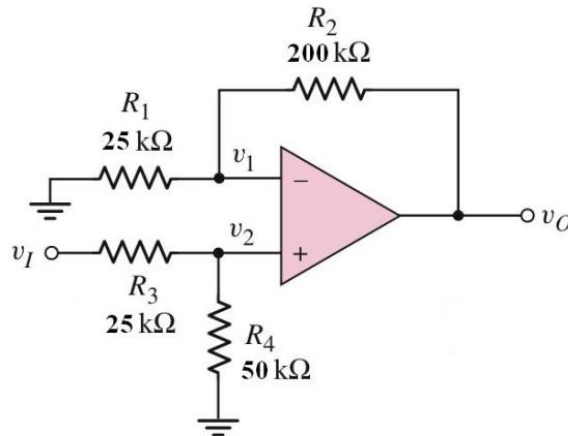


Figure 5b

- (e) For a **generalized summing op-amp** as shown in **Figure 5c** the total output voltage (v_o) is the sum of the individual terms, or

$$v_o = -\frac{R_F}{R_1}v_{I1} - \frac{R_F}{R_2}v_{I2} + \left(1 + \frac{R_F}{R_N}\right)\left(\frac{R_P}{R_A}v_{I3} + \frac{R_P}{R_B}v_{I4}\right)$$

where

$$R_N = R_1 \parallel R_2$$

$$R_P = R_A \parallel R_B \parallel R_C$$

Design a summing op-amp similar to **Figure 5c** to produce the output

$$v_o = -5v_{I1} - 10v_{I2} + 5v_{I3} + 2v_{I4}$$

The **smallest resistor value** allowable in the design is **15 kΩ**.

[8 marks]

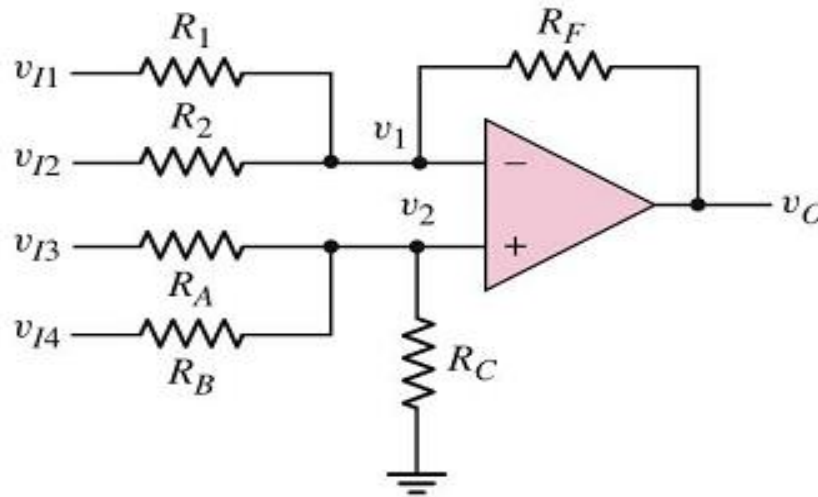


Figure 5c

-END OF QUESTION PAPER-

APPENDIX

BASIC FORMULABJT

$$i_C = I_S e^{v_{BE}/V_T}; \text{npn}$$

$$i_C = I_S e^{v_{EB}/V_T}; \text{pnp}$$

$$i_C = \alpha i_E = \beta i_B$$

$$i_E = i_B + i_C$$

$$\alpha = \frac{\beta}{\beta + 1}$$

;Small signal

$$\beta = g_m r_\pi$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_o = \frac{V_A}{I_{CQ}}$$

MOSFET

;N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k'_n \cdot W}{2 \cdot L}$$

;P – MOSFET

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$

$$i_D = K_p [v_{SG} + V_{TP}]^2$$

$$K_p = \frac{k'_p \cdot W}{2 \cdot L}$$

;Small signal

$$g_m = 2\sqrt{K_n I_{DQ}}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$